/ Revised record

A	2018-12-18				
B	2019-4-20				
C	2019-7-24	1			
D	2021-10-26	4			

/ Descriptions

SOT-363 NPN+PNP

Double silicon NPN and PNP transistor in a SOT-363 Plastic Package.

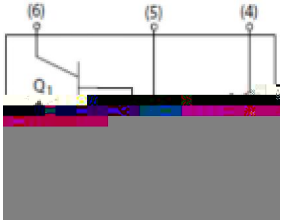
/ Features

Ideal for Low Power Amplification and Switching.HF Product.

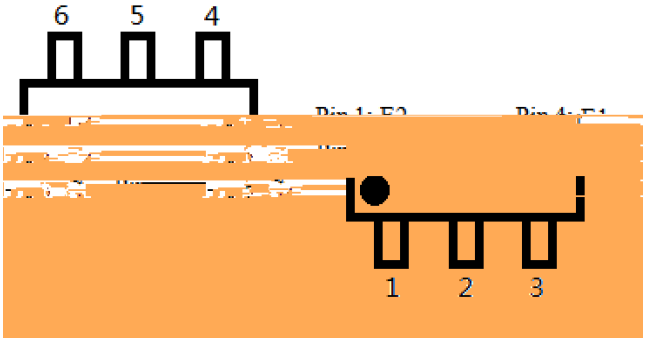
/ Applications

Power amplifier application.

/ Equivalent Circuit



/ Pinning



/ h_{FE} Classifications & Marking

See Marking Instructions.

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Total Power Dissipation	P_d	200	mW
Thermal Resistance, Junction to Ambient	R θ JA	625	/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 150	

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	75	V
Collector to Emitter Voltage	V_{CEO}	40	VE E

BRMMDT2227WS

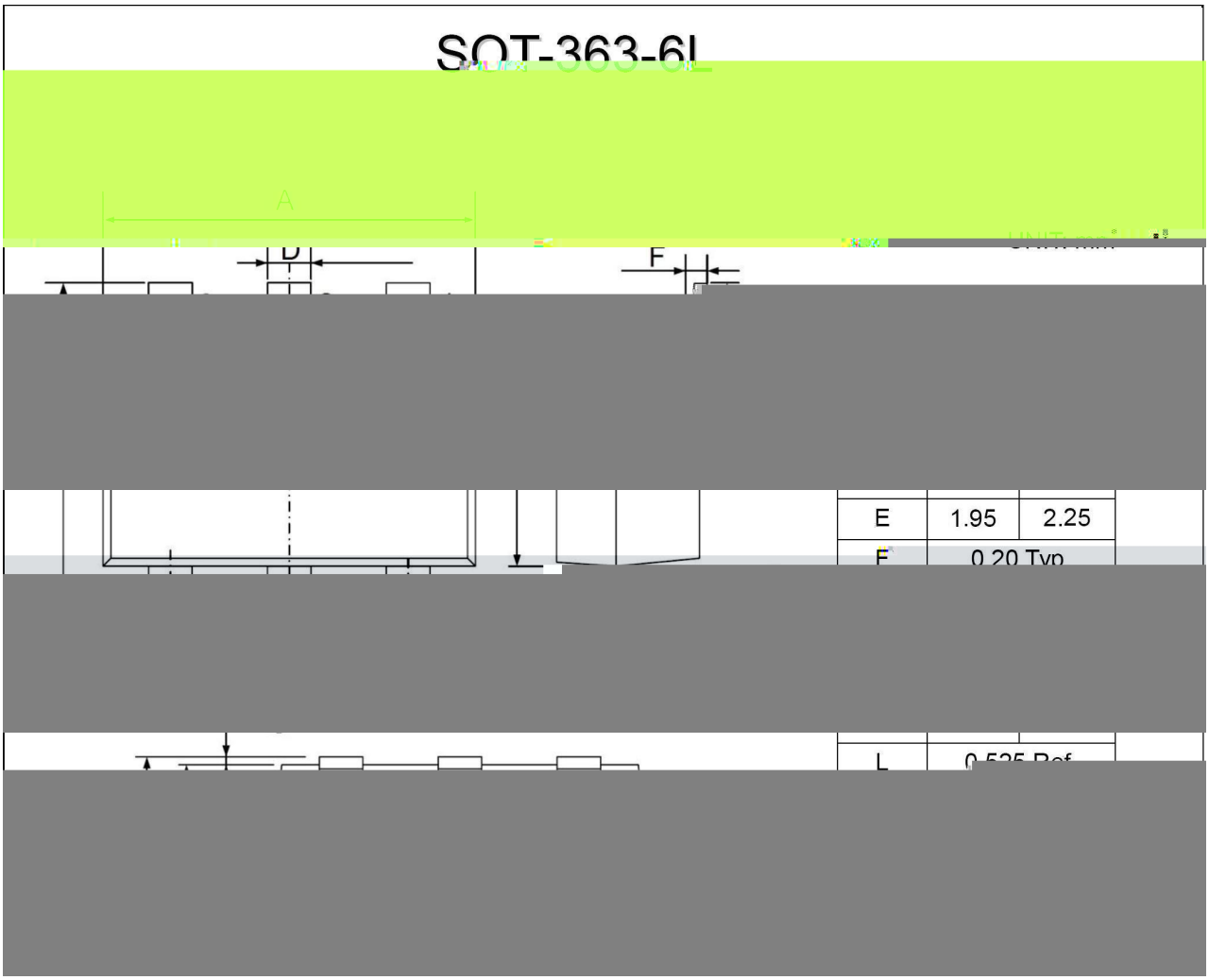
Rev.D Oct.-2021

BRMMDT2227WS

Rev.D Oct.-2021

5

/ Package Dimensions



/ Marking Instructions

Note:

Product Type Code

Lot tD

n

Note:

1.Preheating:150~180℃, Time:60~90sec.

2.Peak Temp.:245±5℃, Duration:5±0.5sec.

3. Cooling Speed: 2~10℃/sec.

Temp.:260±5 Time:10±1 sec

	Dimension " % & (unit ' mm^3)		
Units/Outer Box 只/箱	Reel	Inner Box (	Outer Box)
180000	7″ ×8	180×120×180	390×385×205 04 0 Tm /F94 T5